

Peter Hadley

List of Publications by Year in descending order

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84
papers

5,349
citations

257450

24
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123424

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84
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84
docs citations

84
times ranked

5341
citing authors

#	ARTICLE	IF	CITATIONS
1	Simulation of moisture-induced plasticization in transfer-molded optical sensor packages using a time - temperature - moisture concentration superposition. , 2021, , .		0
2	A time-temperature-moisture concentration superposition principle that describes the relaxation behavior of epoxide molding compounds for microelectronics packaging. International Journal of Polymer Analysis and Characterization, 2020, 25, 467-478.	1.9	9
3	Validation and Optimization of Calculated Stress Fields in Double-Mold Optoelectronics Sensor Packaging. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2020, 10, 974-981.	2.5	1
4	Manipulating drug release from tridimensional porous substrates coated by initiated chemical vapor deposition. Journal of Applied Polymer Science, 2019, 136, 47858.	2.6	14
5	Impact of the NO Anneal on the Microscopic Structure and Chemical Composition of the Si-Face 4H-SiC/SiO ₂ Interface. Advanced Materials Interfaces, 2018, 5, 180022.	3.7	9
6	Electrically detected magnetic resonance of carbon dangling bonds at the Si-face 4H-SiC/SiO ₂ interface. Journal of Applied Physics, 2018, 123, .	2.5	22
7	Characterization of Moisture Uptake in Microelectronics Packaging Materials. , 2018, , .		1
8	Recombination centers in 4H-SiC investigated by electrically detected magnetic resonance and <i>ab initio</i> modeling. Journal of Applied Physics, 2016, 119, .	2.5	15
9	Simulation of the proton implantation process in silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 750-755.	0.8	0
10	An EBIC Model for TCAD Simulation to Determine the Surface Recombination Rate in Semiconductor Devices. IEEE Transactions on Electron Devices, 2016, 63, 4395-4401.	3.0	4
11	Optimizing a sub-wavelength grating lens for large incidence angles. , 2015, , .		0
12	Interface defects in SiC power MOSFETs - An electrically detected magnetic resonance study based on spin dependent recombination. , 2014, , .		6
13	Hydrogen decoration of radiation damage induced defect structures. , 2014, , .		1
14	H ⁺ implantation profile formation in m:Cz and Fz silicon. , 2014, , .		2
15	Electrically detected magnetic resonance study of defects created by hot carrier stress at the SiC/SiO ₂ interface of a SiC <i>n</i> -channel metal-oxide-semiconductor field-effect transistor. Applied Physics Letters, 2014, 105, .	3.3	4
16	Investigations on CMOS photodiodes using scanning electron microscopy with electron beam induced current measurements. , 2014, , .		1
17	An EBIC and SRP study on thermal donors in proton implanted p-type magnetic Czochralski silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1583-1588.	0.8	0
18	Electrically detected magnetic resonance study on defects in Si pn-junctions created by proton implantation. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1593-1596.	0.8	0

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19	Depletion of superjunction power MOSFETs visualized by electron beam induced current and voltage contrast measurements. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014, 11, 1707-1710.	0.8	2
20	High dose proton implantations into silicon: a combined EBIC, SRP and TEM study. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014, 11, 1545-1550.	0.8	1
21	Investigation of Doping Type Conversion and Diffusion Length Extraction of Proton Implanted Silicon by EBIC. <i>ECS Transactions</i> , 2013, 50, 115-120.	0.5	2
22	Imaging Superjunctions in CoolMOS Devices Using Electron Beam Induced Current. <i>ECS Transactions</i> , 2012, 49, 475-481.	0.5	1
23	Reaction dynamics of diffusion soldering with the eutectic Au-Sn alloy on copper and silver substrates. <i>Intermetallics</i> , 2012, 20, 87-92.	3.9	21
24	Suppression of Interdiffusion in Copper/Tin Thin Films. <i>Journal of Materials Engineering and Performance</i> , 2012, 21, 1724-1727.	2.5	10
25	Thermodynamic properties of separable square-wave potentials. <i>Physica B: Condensed Matter</i> , 2011, 406, 4373-4380.	2.7	5
26	Electron Beam-Induced Current (EBIC) in solution-processed solar cells. <i>Scanning</i> , 2011, 33, 1-6.	1.5	42
27	In-situ XRD and FIB microscopy studies of the dynamics of intermetallic phase formation in thin layer Cu/Sn films for low-temperature isothermal diffusion soldering. <i>Materials Research Society Symposia Proceedings</i> , 2011, 1318, 1.	0.1	3
28	Organic field-effect transistors (OFETs) of highly oriented films of dithiophene-tetrathiafulvalene prepared by zone casting. <i>Organic Electronics</i> , 2008, 9, 143-148.	2.6	49
29	Sub-500/spl deg/C solid-phase epitaxy of ultra-abrupt p ⁺ -silicon elevated contacts and diodes. <i>IEEE Electron Device Letters</i> , 2006, 27, 341-343.	3.9	18
30	Large Photoresponsivity in High-Mobility Single-Crystal Organic Field-Effect Phototransistors. <i>ChemPhysChem</i> , 2006, 7, 86-88.	2.1	70
31	Low-Temperature Solid-Phase Epitaxy of Defect-Free Aluminum p ⁺ -doped Silicon for Nanoscale Device Applications. <i>Materials Research Society Symposia Proceedings</i> , 2006, 940, 1.	0.1	1
32	Electrical transport measurements on self-assembled organic molecular wires. <i>Journal of Chemical Physics</i> , 2006, 124, 154704.	3.0	18
33	Field Emission as Transducer for Sub-micron and Nano Resonators. , 2006, , .		0
34	Electrochemical Growth of Organic Conducting Microcrystals of Tetrathiafulvalene Bromide. <i>Small</i> , 2005, 1, 806-808.	10.0	24
35	Single-crystal organic field-effect transistors based on dibenzo-tetrathiafulvalene. <i>Applied Physics Letters</i> , 2005, 86, 012110.	3.3	130
36	Importance of Intermolecular Interactions in Assessing Hopping Mobilities in Organic Field Effect Transistors: A Pentacene versus Dithiophene-tetrathiafulvalene. <i>Journal of the American Chemical Society</i> , 2004, 126, 6544-6545.	13.7	161

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37	Correlation between Crystal Structure and Mobility in Organic Field-Effect Transistors Based on Single Crystals of Tetrathiafulvalene Derivatives. <i>Journal of the American Chemical Society</i> , 2004, 126, 8546-8553.	13.7	265
38	Field effect transistors based on poly(3-hexylthiophene) at different length scales. <i>Nanotechnology</i> , 2004, 15, S265-S269.	2.6	73
39	Towards supramolecular electronics. <i>Synthetic Metals</i> , 2004, 147, 43-48.	3.9	44
40	Temperature dependence of the electrical properties of single-crystals of dithiophene-tetrathiafulvalene (DT-TTF). <i>Synthetic Metals</i> , 2004, 146, 265-268.	3.9	21
41	High Mobility of Dithiophene-Tetrathiafulvalene Single-Crystal Organic Field Effect Transistors. <i>Journal of the American Chemical Society</i> , 2004, 126, 984-985.	13.7	327
42	Electrical Transport Study of Phenylene-Based π -Conjugated Molecules in a Three-Terminal Geometry. <i>Annals of the New York Academy of Sciences</i> , 2003, 1006, 122-132.	3.8	10
43	Logic circuits based on carbon nanotubes. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2003, 16, 42-46.	2.7	36
44	Absence of Strong Gate Effects in Electrical Measurements on Phenylene-Based Conjugated Molecules. <i>Nano Letters</i> , 2003, 3, 113-117.	9.1	145
45	Simulating Hybrid Circuits of Single-Electron Transistors and Field-Effect Transistors. <i>Japanese Journal of Applied Physics</i> , 2003, 42, 6467-6472.	1.5	67
46	Quantum superposition of charge states on capacitively coupled superconducting islands. <i>Physical Review B</i> , 2003, 67, .	3.2	2
47	Superconducting single-electron push-pull amplifier stage. <i>Review of Scientific Instruments</i> , 2002, 73, 491-492.	1.3	0
48	Logic circuits with carbon nanotubes. <i>AIP Conference Proceedings</i> , 2002, , .	0.4	9
49	Logic Circuits with Carbon Nanotube Transistors. <i>Science</i> , 2001, 294, 1317-1320.	12.6	2,523
50	Single-electron inverter. <i>Applied Physics Letters</i> , 2001, 78, 1140-1142.	3.3	68
51	Charge spectrometry with a strongly coupled superconducting single-electron transistor. <i>Physical Review B</i> , 2001, 64, .	3.2	5
52	Title is missing!. <i>Journal of Low Temperature Physics</i> , 2000, 118, 325-332.	1.4	1
53	Quantum nanocircuits: chips of the future?. , 2000, , 1-18.		0
54	Negative differential resistance due to single-electron switching. <i>Applied Physics Letters</i> , 1999, 74, 1042-1044.	3.3	67

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55	3etunneling processes in a superconducting single-electron tunneling transistor. Physical Review B, 1998, 58, 15317-15320.	3.2	33
56	Single-electron tunneling devices. , 1998, , .		4
57	<title>New process for nanometer-scale devices</title>. , 1997, , .		0
58	High T/sub c/ superconducting CPW bandstop filters for radio astronomy front ends [YBa/sub 2/Cu/sub 3/O/sub 7/-LaAlO/sub 3/]. IEEE Transactions on Applied Superconductivity, 1997, 7, 3489-3491.	1.7	12
59	High Tc superconducting CPW bandstop filters. , 1996, 6, 292.		5
60	Ginzburgâ€“Landau theory of Josephson field effect transistors. Applied Physics Letters, 1996, 69, 2432-2434.	3.3	5
61	Broadband singleâ€“electron tunneling transistor. Applied Physics Letters, 1996, 68, 2014-2016.	3.3	48
62	Fabrication of multilayer singleâ€“electron tunneling devices. Applied Physics Letters, 1995, 66, 305-307.	3.3	66
63	Electric field effect in Sm/sub 1-x/Ca/sub x/Ba/sub 2/Cu/sub 3/O/sub y/ bicrystal junctions. IEEE Transactions on Applied Superconductivity, 1995, 5, 2879-2882.	1.7	15
64	Deep-submicron structures in YBCO: fabrication and measurements. IEEE Transactions on Applied Superconductivity, 1995, 5, 1448-1451.	1.7	10
65	Interference of Flux-Quanta. , 1995, , 529-539.		0
66	Dynamics of 1-D parallel arrays of underdamped Josephson junctions. Physica B: Condensed Matter, 1994, 194-196, 1667-1668.	2.7	2
67	High IcRn products and hysteretic behavior of YBCO/Au/YBCO Josephson junctions. Physica C: Superconductivity and Its Applications, 1994, 235-240, 3243-3244.	1.2	5
68	Electric field induced superconductivity in an overdoped cuprate superconductor. Physica C: Superconductivity and Its Applications, 1994, 235-240, 2097-2098.	1.2	23
69	MBE synthesis of YBa/sub 2/Cu/sub 3/O/sub y/ superconducting thin films. IEEE Transactions on Applied Superconductivity, 1993, 3, 1524-1527.	1.7	6
70	Critical currents in submicron YBa/sub 2/Cu/sub 3/O/sub 7/ lines. IEEE Transactions on Applied Superconductivity, 1993, 3, 2983-2985.	1.7	25
71	In-situ growth of YBa2Cu3Oy superconducting films by reactive coevaporation at low pressure using ozone. , 1992, , 383-388.		0
72	High quality flux control system for electron gun evaporation. IEEE Transactions on Magnetics, 1991, 27, 1467-1470.	2.1	3

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73	Single Cooper pair pump. European Physical Journal B, 1991, 85, 349-355.	1.5	70
74	In situ growth of high temperature superconductor thin films with evaporation techniques using an ozone jet. IEEE Transactions on Magnetics, 1991, 27, 1013-1016.	2.1	4
75	Attractor crowding in oscillator arrays. Physical Review Letters, 1989, 62, 1335-1338.	7.8	236
76	Noise driven fluctuations of Josephson junction series arrays. IEEE Transactions on Magnetics, 1989, 25, 1088-1091.	2.1	3
77	Phase locking of Josephson-junction series arrays. Physical Review B, 1988, 38, 8712-8719.	3.2	277
78	Phase locking of Josephson junction arrays. Applied Physics Letters, 1988, 52, 1619-1621.	3.3	59
79	Dynamical states and stability of linear arrays of Josephson junctions. Applied Physics Letters, 1987, 50, 621-623.	3.3	111
80	Stability of Coherent Oscillations in Josephson Junction Arrays. Japanese Journal of Applied Physics, 1987, 26, 1419.	1.5	8
81	An Extended EDMR Setup for SiC Defect Characterization. Materials Science Forum, 0, 740-742, 365-368.	0.3	1
82	Multiple Proton Implantations into Silicon: A Combined EBIC and SRP Study. Solid State Phenomena, 0, 205-206, 311-316.	0.3	3
83	Influence of Oxide Processing on the Defects at the SiC-SiO ₂ Interface Measured by Electrically Detected Magnetic Resonance. Materials Science Forum, 0, 858, 643-646.	0.3	3
84	Electrical-stress driven oxidation in 940 nm oxide-confined VCSEL. Semiconductor Science and Technology, 0, , .	2.0	2